~~**What is claimed is:**~~

CLAIMS

1. A method of operating a spatial deposition tool, the method comprising:

providing a processing chamber comprising *x* number of spatially separated isolated processing stations, the processing chamber having a processing chamber temperature and each processing station independently having a processing station temperature, the processing chamber temperature different from the processing station temperatures;

rotating a substrate support assembly having a plurality of substrate support surfaces aligned with the *x* number of spatially separated isolated processing stations *rx* so that each substrate support surface rotates (360/*x*) degrees in a first direction to an adjacent substrate support surface, *r* being a whole number greater than or equal to 1; and

rotating the substrate support assembly *rx* times so that each substrate support surface rotates (360/*x*) degrees in a second direction to the adjacent substrate support surface~~.~~;

wherein each of the plurality of substrate support surfaces respectively comprise a heater, and

wherein a sealing platform is connected to the heater at a position below and surrounding the heater.

2. The method of claim 1, wherein *x* is an integer in a range of from 2 to 10.

3. The method of claim 1, wherein *r* is in the range of 1 to 10.

4. The method of claim 1, wherein *r* is 1, 2, 3 or 4.

~~4.~~5. The method of claim 1, wherein the plurality of substrate support surfaces are substantially coplanar.

~~1. The method of claim 4, wherein the plurality of substrate support surfaces comprise heaters.~~

~~5.~~6. The method of claim 1, further comprising controlling one or more of the processing chamber temperature or the processing station temperatures.

~~6.~~7. The method of claim 1, further comprising controlling ~~the~~ speed of rotation of the plurality of substrate support assembly.

~~7.~~8. ~~A~~A method of operating a spatial deposition tool, the method comprising:

providing a processing chamber comprising *x* number of spatially separated isolated processing stations, the processing chamber having a processing chamber temperature and each processing station independently having a processing station temperature, the processing chamber temperature different from the processing station temperatures;

rotating a substrate support assembly having a plurality of substrate support surfaces aligned with the *x* number of spatially separated isolated processing stations (360/*x*) degrees in a first direction to an adjacent substrate support surface;

rotating the substrate support assembly (360/*x*) degrees in a second direction to the adjacent substrate support surface, wherein the rotations in the first direction and the rotations in the second direction are repeated *n* times, with *n* being a whole number greater than or equal to 1;

rotating the substrate support assembly (360/x) degrees in a first direction two times;

rotating the substrate support assembly (360/x) degrees in the first direction and then rotating the substrate support assembly (360/x) degrees in the second direction, the rotations in the first direction and the second direction are repeated *m* times, with *m* being a whole number greater than or equal to 1; and

rotating the substrate support assembly (360/x) degrees in the second direction~~.~~;

wherein each of the plurality of substrate support surfaces respectively comprise a heater, and

wherein a sealing platform is connected to the heater at a position below and surrounding the heater.

~~8.~~9. The method of claim 8, wherein *x* is an integer in a range of from 2 to 10.

~~9.~~10. The method of claim 8, wherein the plurality of substrate support surfaces are substantially coplanar.

~~10.~~11. The method of claim 8, further comprising controlling one or more of the processing chamber temperature or the processing station temperatures.

~~11.~~12. The method of claim 8, further comprising controlling ~~the~~ speed of rotation of the plurality of substrate support assembly.

~~12.~~13. A method of forming a film, the method comprising:

loading at least one wafer onto *x* number of substrate support surfaces in a substrate support assembly, each of the substrate support surfaces aligned with *x* number of spatially separated isolated processing stations;

rotating the substrate support assembly *rx* so each substrate support surface rotates (360/*x*) degrees in a first direction to an adjacent substrate support surface, *r* being a whole number greater than or equal to 1;

rotating the substrate support assembly *rx* times so that each substrate support surface rotates (360/*x*) degrees in a second direction to the adjacent substrate support surface; and

at each processing station, exposing a top surface of the at least one wafer to a process condition to form a film having a substantially uniform thickness~~.~~;

wherein each of the substrate support surfaces respectively comprise a heater, and

wherein a sealing platform is connected to the heater at a position below and surrounding the heater.

~~13.~~14. The method of claim 13, wherein the at least one wafer is stationary when the film is formed.

~~14.~~15. The method of claim 13, wherein *x* is an integer in a range of from 2 to 10~~, and wherein *r* is in the range of 1 to 10.~~.

16. The method of claim 13, wherein *r* is in the range of 1 to 10.

17. The method of claim 13, wherein *r* is 1, 2, 3 or 4.

18. The method of claim 13, wherein the substrate support surfaces further comprise electrostatic chucks.